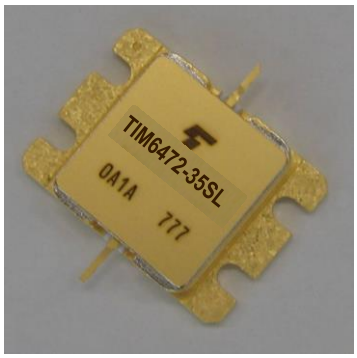
MICROWAVE POWER GaAs FET

TIM6472-35SL

FEATURES



- **BROAD BAND INTERNALLY MATCHED FET**
- **HIGH POWER**
  P1dB= 45.5dBm at 6.4GHz to 7.2GHz
- **HIGH GAIN**
  G1dB= 8.0dB at 6.4GHz to 7.2GHz
- **LOW INTERMODULATION DISTORTION**
  IM3= -45dBc at Pout= 35.0dBm
  Single Carrier Level
- **HERMETICALLY SEALED PACKAGE**

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 8.0A f = 6.4 to 7.2GHz	dBm	45.0	45.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.0	8.0	—
Drain Current	IDS1		A	—	8.0	9.0
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	37	—
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 35.0dBm, Δf= 5MHz (Single Carrier Level)	dBc	-42	-45	—
Drain Current	IDS2		A	—	8.0	9.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	—	—	100

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 10.5A	S	—	6.5	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 140mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	20	—
Gate-Source Breakdown Voltage	VGSO	IGS= -420μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	1.0	1.3

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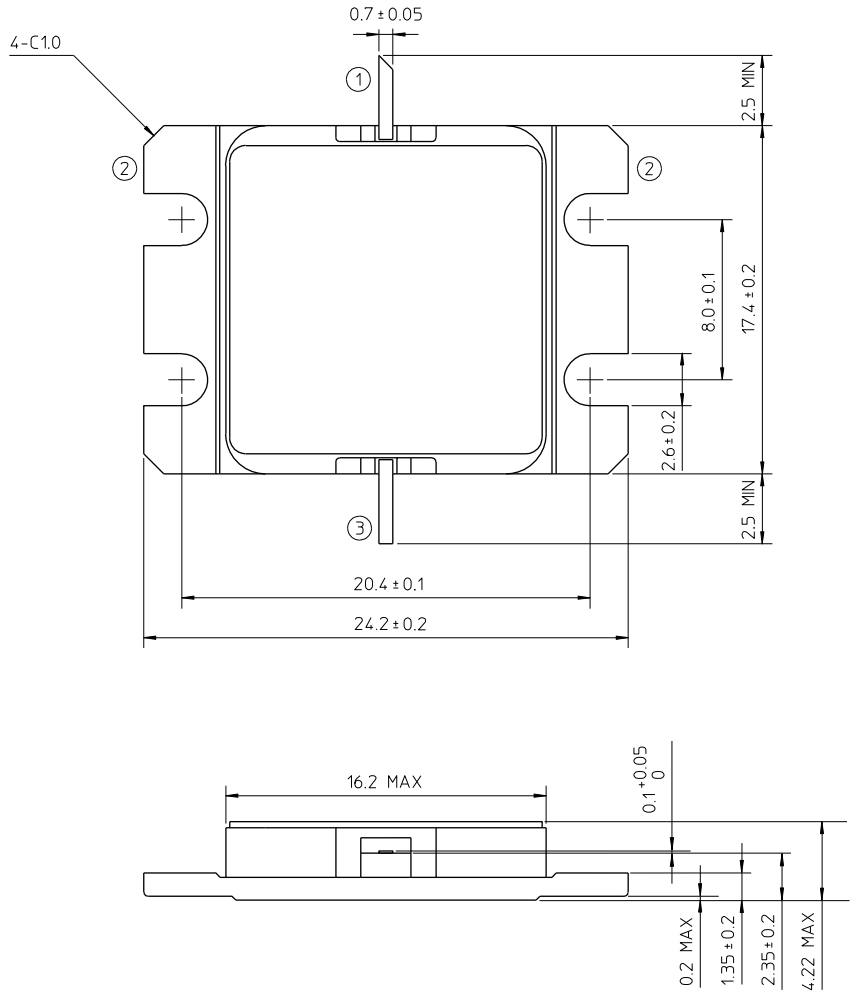
ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	20
Total Power Dissipation (Tc= 25°C)	PT	W	115.4
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)



Unit in mm

① Gate
② Source
③ Drain

HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

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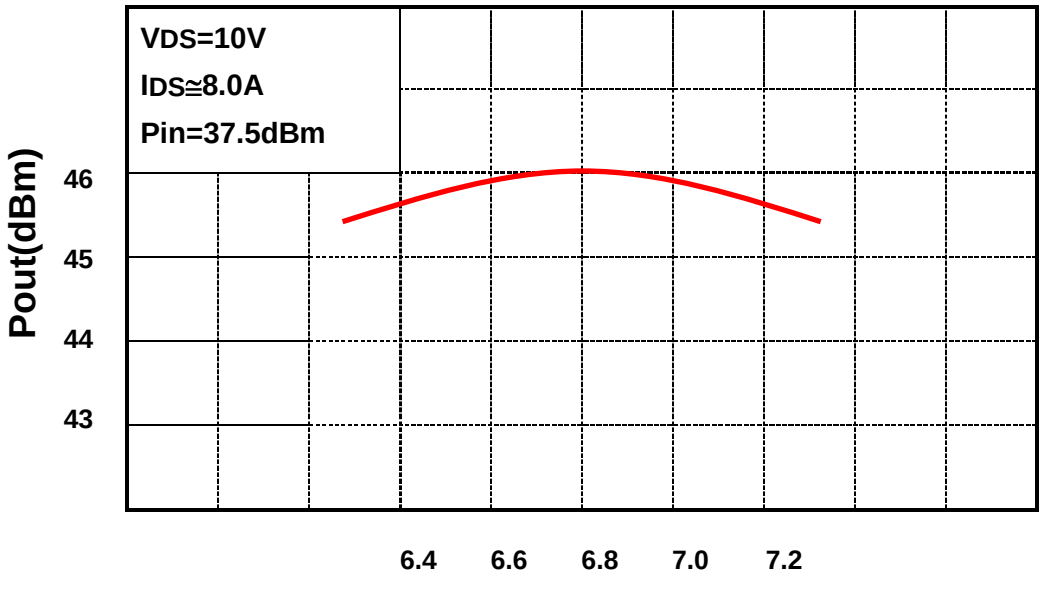
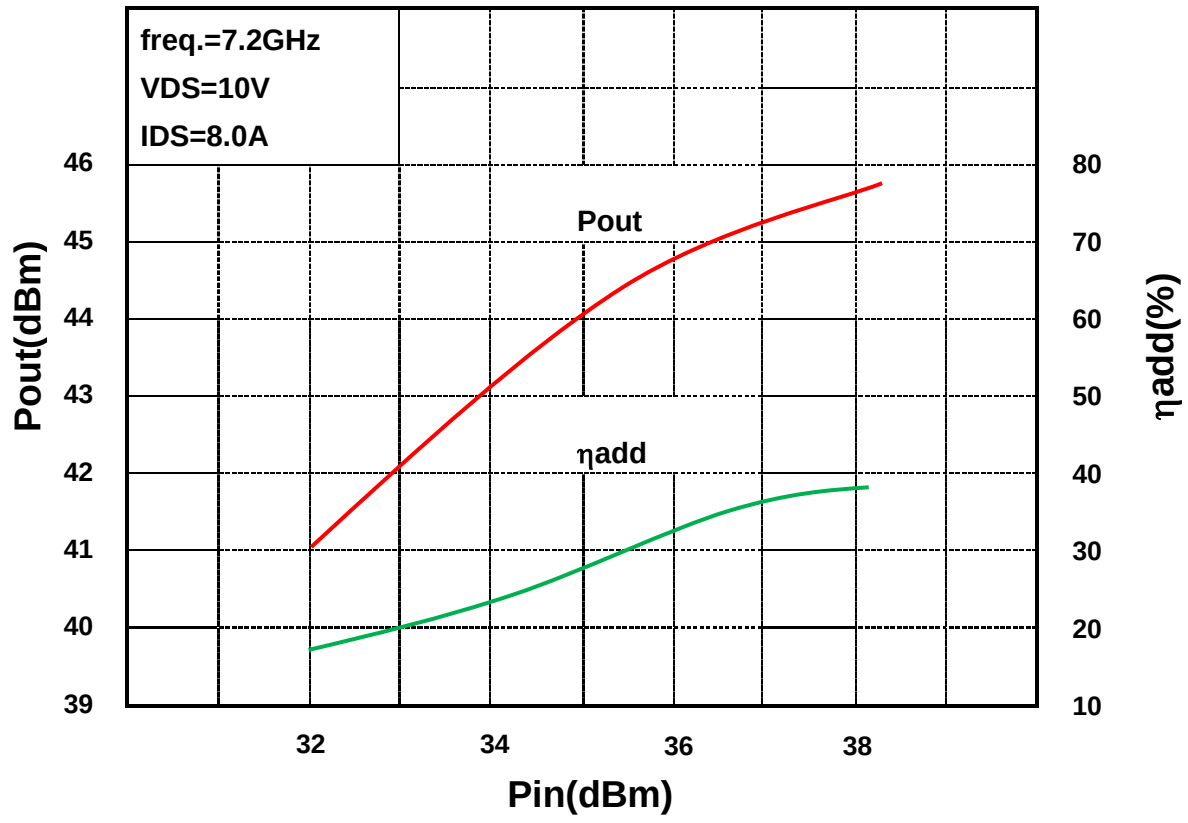
RF PERFORMANCE

Output Power (Pout) vs. Frequency



Output Power(Pout) vs. Input Power(Pin)



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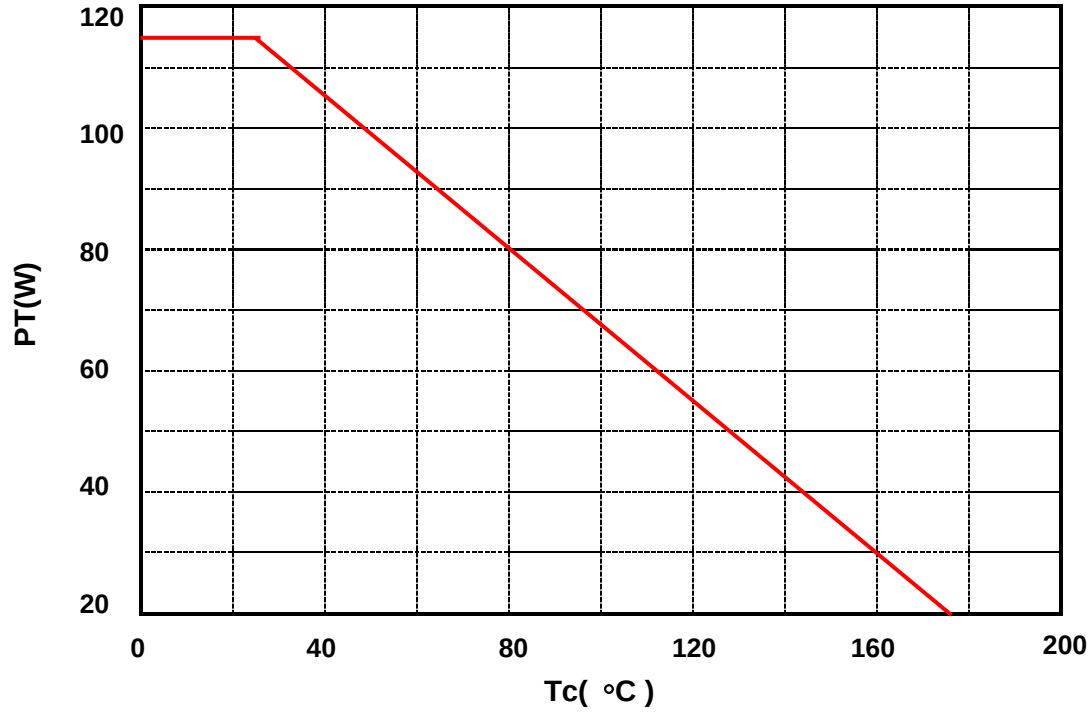
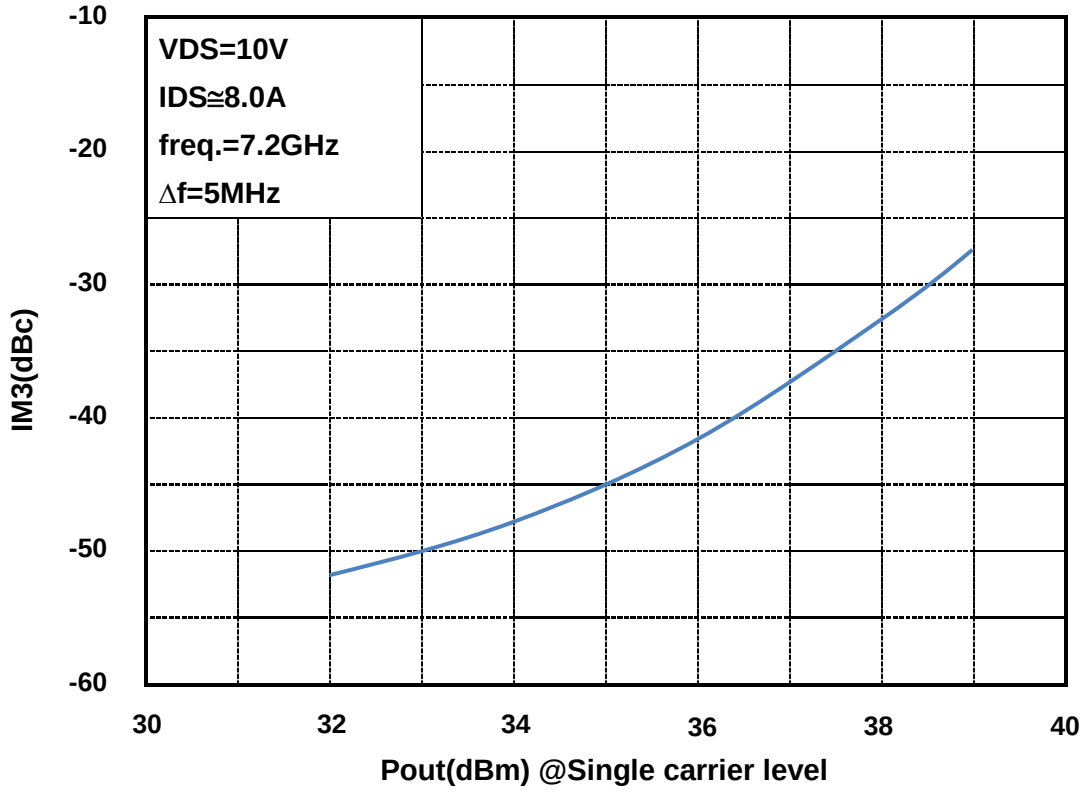
Power Dissipation(PT) vs. Case Temperature(Tc)



IM3 vs. Power Characteristics



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